

# Silicon Carbide Material with Power Electronic Control Devices

<sup>1</sup>Y.S. Ravikumar and <sup>2</sup>K.S. Gurumurthy

<sup>1</sup>Research scholar, faculty of ECE, Dr. MGR University, Chennai-95

<sup>2</sup>Professor, faculty of Electronics and CSE, UVCE, Bangalore-01

## Abstract

Silicon carbide is a physically robust semiconductor whose crystal lattice is a cross between pure silicon and pure diamond. Silicon is the foundation of the modern microelectronics industry, and the most highly developed manufacturing technology in the history of mankind. Semiconducting diamond has electronic properties far superior to silicon, but, it has not been developed commercially, because its extreme material stability makes ordinary semiconductor fabrication techniques impractical. In this paper work, SiC is used for high temperature environments because of its high bandgap energy to create electron-hole (e-h) pairs in the material. The bandgap of SiC is about three times higher than silicon, but, since the e-h pair generation rate decreases exponentially with bandgap, the average density of e-h pairs in SiC at room temperature (the intrinsic carrier concentration) is sixteen orders-of-magnitude lower than silicon.

## Keywords

*Silicon Carbide, SiC, Power Electronics Control Device, Wide bandgap semiconductors (WBS).*

## 1. INTRODUCTION

Silicon carbide (SiC) is the perfect cross between silicon and diamond. The crystal lattice of SiC is identical to silicon and diamond, but exactly half the lattice sites are occupied by silicon atoms and half by carbon atoms. Like-diamond SiC has electronic properties superior to silicon, but, unlike diamond it is also manufacturable. The thermal leakage current (dark current) in SiC is sixteen orders-of-magnitude lower as well. As temperature increases, the leakage current increases, but, the temperature where the leakage current would disrupt circuit operation is over 1000 °C in SiC, compared to about 250 °C in silicon. The SiC electronic revolution began in the early 1990's when single-crystal wafers became commercially available for the first time. During the intervening years, many different electronic devices have been demonstrated in SiC, with performance often exceeding the theoretical limits of silicon. These include pn diodes, MOS field-effect transistors (MOSFETs), metal-semiconductor field-effect transistors (MESFETs), and bipolar transistors (BJTs), as well as specialized devices such as CCD imagers, Schottky diodes, static induction transistors (SITS), and impact-ionization- avalanche-transit-time (MATT) microwave oscillators. These early digital logic gates and linear elements are based on n-channel

MOS technology, but, quickly followed by more sophisticated CMOS integrated circuits.

## 2. Applications of SiC

### 2.1 SiC – a widely used material

The material qualities of SiC have great potential, before the emergence of microelectronics applications based on SiC, to unique mechanical properties, so SiC is used as an abrasive in sand, in polishing agents or in cutting tools. SiC is one of the hardest materials known to man, only diamond and boron nitride are harder. The short bond length of 1.89 Å between 'Si' and 'C' atoms result is in high bond strength and excellent hardness. However, this makes SiC wafers difficult to cut and polish. The strong bonds do also create a large bandgap that gives SiC's high refractive index accompanied by a broad transparency over the visible spectrum, optical brilliance, and resistance to chemical and abrasive attack. Recently high-purity, almost colorless Moissanite crystals become available, leading to the development of SiC gemstone that have a beneficial influence on SiC semiconductor. Due to relatively low density, SiC can be used even in space applications, e.g. for ultra-lightweight mirrors. It is also appropriate for bearings with the hardness and toughness.

### 2.2 Wide bandgap semiconductors

The wide range applications of SiC, is the most promising area is semiconductor processing. The wide bandgap materials are in many respects superior to silicon due to their physical and electrical properties. The properties of different wide bandgap semiconductors, selected from the viewpoint of microelectronics applications. For e.g. in SiC the probability of thermal excitation of an electron over the bandgap is  $10^{-26}$  at room temperature, i.e. there are no thermally excited electrons in the conduction band. The wide bandgap is also accompanied by considerably higher breakdown voltage as compared to silicon. This means that for power devices with similar blocking voltage capabilities, the one made of silicon must have about 100 times lower doping level in a 10 times thicker layer, as compared to a SiC device.

### 2.3 SiC for microelectronics applications

The wide bandgap semiconductor having silicon dioxide ( $\text{SiO}_2$ ) as native oxide, similarly to silicon is studied in SiC.  $\text{SiO}_2$  as a dielectric is needed for surface passivation of SiC devices, as well as for a gate material in metal-oxide-semiconductor field-effect transistors (MOSFETs) and related structures. Silicon dioxide can be formed by simple wet or dry oxidation of SiC.

### 2.4 High voltage devices

SiC high voltage devices can be realized on much thinner drift layers than for Si and GaAs diodes, achieving high breakdown voltage as well as lower on-resistance and good results have been demonstrated with a steady improvement in performance. SiC junction Schottky barrier diodes (JBS) are interesting in the 600 – 3300V blocking voltage regime. SiC Schottky diodes suffer from a rather high reverse leakage current, which is suppressed in JBS diodes. Moreover, in JBS diodes, the switching frequency and the blocking voltage/surge current capabilities are promising features compared to PiN and Schottky diodes.

### 2.5 RF power devices

SiC devices have shown considerable improvement and superior RF power performance to those available in Si or GaAs devices. The RF power available from an impact ionization avalanche transit time (IMPATT) diode in SiC is  $\sim 100$  times higher than in Si or GaAs. The high temperature and/or high power SiC electronic devices would enable revolutionary improvements to aerospace systems, even without cooling systems. Replacement of hydraulic controls and auxiliary power units with distributed smart electro-mechanicals controls capable of harsh-ambient operation enables substantial jet-aircraft weight savings, and reduced maintenance.

## 3. Crystal Structure and Polytypism

The SiC's crystalline structure and its polytypic nature influence of polytypism on the physical properties of SiC. Silicon carbide is a binary compound containing equal amount of 'Si' and 'C', where, Si-C bonds are nearly covalent, with an ionic contribution of 12% (Si positively, 'C' negatively charged). The smallest building element of any SiC lattice is a tetrahedron of a Si (C) atom surrounded by four C (Si) atoms in strong  $\text{sp}^3$ -bonds. Therefore, the first neighbor shell configuration is identical for all atoms in any crystalline structure of SiC. The basic elements of SiC crystals is shown in Figure 1.

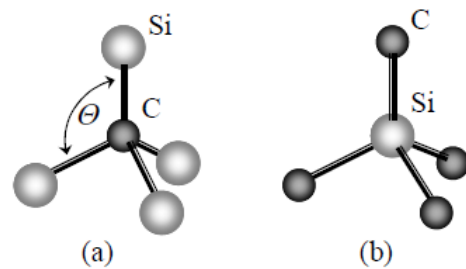


Fig. 1 Basic elements of SiC crystals: Tetrahedrons containing (a) one C and four Si (b) one Si and four C atoms

## 4. Power electronic systems for control ENERGY

Power electronic systems for controlling and converting electrical energy have become the workhorse of modern society in many applications. Put quite simply, power is everywhere. For eg., power electronic systems play a dominant role in making more efficient use of electric power in many appliances, both in industry and in the home. The use of power converters for variable speed drives results in energy savings and recovers the additional converter cost within a short period of time. Power electronics plays a very important role in traction by enabling the use of electric cars and trains and can be considered as workhorse of robotics and automated manufacturing systems. The importance of effective energy conversion control, including power generation from renewable and environment-friendly energy sources, has increased due to rising energy demand.

Power semiconductor devices are the key electronic components used in power electronic systems. Many power semiconductor devices have been developed and produced since the invention of the thyristor, which marked the beginning of the modern era of power electronics, which can be called the solid state power electronics revolution. The introduction of neutron transmutation doping (NTD) of silicon is enabled the development of high voltage large-area diodes and thyristors. Power semiconductors play a leading role in the progress of power electronics, since they are essential for satisfying the constantly growing demands on performance, cost and reliability. Advances in power semiconductor technology have improved the efficiency, size, weight and cost of power electronic systems. Cost reduction has provided an important motivation for developing better switching devices in power converters. Power integrated circuits (PIC) have been developed as a result of recent advances in circuit integration technology, and this has led to a significant improvement in reliability and to reductions in

size, weight and cost. This has extended the use of power converters for portable, automotive and aerospace applications. There are still many challenges connected with optimizing the construction of power semiconductor devices and integrated systems for emerging new applications. Innovation in the area of power semiconductors requires a concerted multi-disciplinary effort linking physicists, engineers, technologists, circuit designers and end-users. The most important directions in present-day research and development are:

- (i) improved switches - higher blocking voltage, higher on-state current density, higher switching frequency, easy to drive
- (ii) power integration - integration of logic and power circuits in a single chip with increasing applications in the area of power management, automotive, telecommunication, power supply, etc.
- (iii) improvements in reliability – solutions in device construction and technology, thermal management and
- (iv) packaging, better knowledge of how to use power semiconductors safely.

Efforts at improving power semiconductor devices from the current state-of-the-art is, ultimately, fuelled by increasing cost pressure, as high reliability is nowadays taken for granted. Cost reduction can essentially be achieved by:

- (i) Lower component cost, i.e., higher output current for a given device area;
- (ii) Lower component count. In the high voltage arena, in essence this means larger devices, and/or higher voltages per device
- (iii) Reduced cost and size of the entire power electronic system, i.e., of the cooling system, the filter unit, the mechanical structure, and all auxiliary parts.

Silicon as a well-established starting material that has already met these requirements for more than 50 years. However, for some applications wide band-gap materials like SiC and GaN offer the potential to overcome both the temperature limitations and the power management limitations of Si.

## 5. Semiconductor switching devices

The ideal switch should have: very high blocking voltage in offstate, very low on-state resistance, very short (zero) turn-on and turn-off times, very low turn-on and turn-off power dissipation. The switch should have only one gate, easy control and it should be in the off-state without a

controlling signal. In real power semiconductor device structures, described in details in e.g. in [1],[2], the high blocking voltage is connected with the existence of a thick space charge region (depletion layer) at the PN junction that spreads with increasing voltage into a low doped area of the structure. A PN junction breakdown occurs if the electric field in the depletion layer reaches its critical value  $E_{crit}$ . From simple theory, the breakdown voltage  $V_{BR}$  depends on donor concentration  $N_D$  in a low doped area, as

$$V_{BR} = \frac{\epsilon_0 \epsilon_r E_{crit}^2}{2eN_D} \quad \dots (1)$$

The breakdown voltage may also be expressed as,

$$V_{BR} = \xi w_D E_{crit} \quad \dots (2)$$

where  $w_D$  is the thickness of the high resistivity (low doped) region and  $0.5 < \xi < 1$  ( $\xi = 0.5$  for the non punch through case,  $\xi = 1$  for an ideal PIN structure). Therefore, the thickness of the structure increases with increasing blocking voltage, as shown in Figure.2. Perfect junction surface termination is necessary in order to obtain a high breakdown voltage.

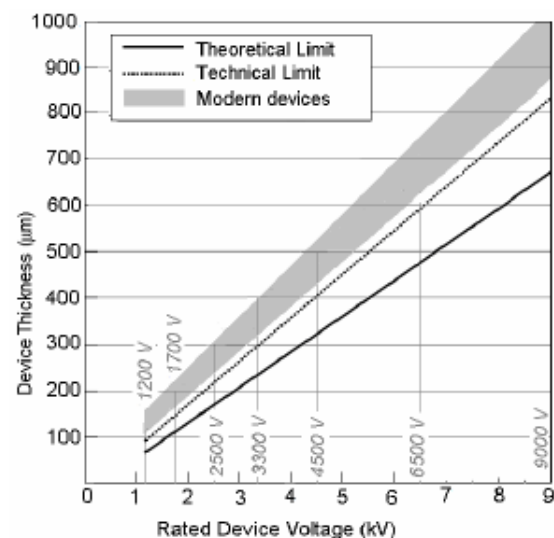


Fig.2 Comparison between the minimum device thickness and breakdown voltage

A common design objective of power semiconductor switches is to optimize the combination of conduction losses and switching losses (in the form of heat), because the maximum operating temperature  $T_{jmax}$  is limited to prevent thermal breakdown. The maximum power losses are limited by,

$$P_{AVmax} \leq \frac{T_{jmax} - T_a}{R_{thja}} \quad \dots (3)$$

$T_{j\max}$  is the maximum junction temperature,  $T_a$  is the temperature of the ambient, and  $R_{thja}$  refers to the thermal resistance between the semiconductor junction and the ambient. Thus, the maximum current in a particular application is influenced not only by the characteristics of the device but also by the thermal resistance of the encapsulation and the thermal resistance of the heat sink. The maximum operating temperature  $T_{j\max}$  decreases with the device blocking voltage [3][4], as shown in Figure 3.

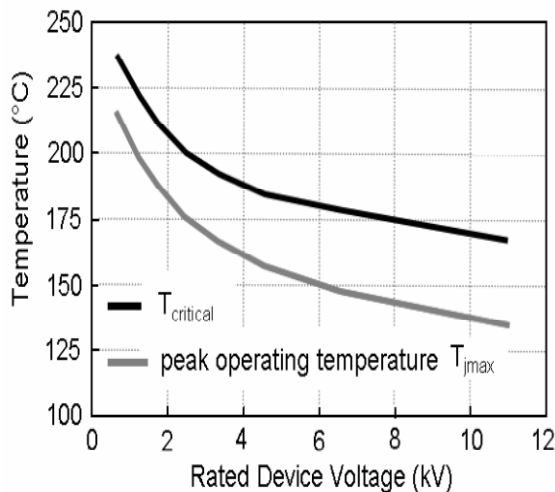


Fig.3 Critical thermal runaway temperature and the estimated maximum safe operating temperature  $T_{j\max}$  of silicon devices

The power losses of a hard switching device operating at frequency  $f$  can be expressed by

$$P_{AV} = \psi I_{on} V_{on} + f(W_{on} + W_{off}), \quad \dots (4)$$

where,  $I_{on}$  is on-state current,  $V_{on}$  is on-state voltage,  $W_{on}$  are onstate losses,  $W_{off}$  are off-state losses and  $\psi$  represents the duty cycle. Eqs. (3) and (4) provide limits for device application, as demonstrated in Figure 4. Some important features of the most important types of switching devices are discussed bellow.

The current and future power semiconductor devices developmental direction is shown in Figure 5. High temperature operation capability and low forward voltage drop operation can be obtained if silicon is replaced by silicon carbide material for producing power devices. The silicon carbide has a higher band gap than silicon. Hence, higher breakdown voltage devices could be developed. Silicon carbide devices have excellent switching characteristics and stable blocking voltages at higher temperatures. But, the silicon carbide devices are still in the very early stages of development.

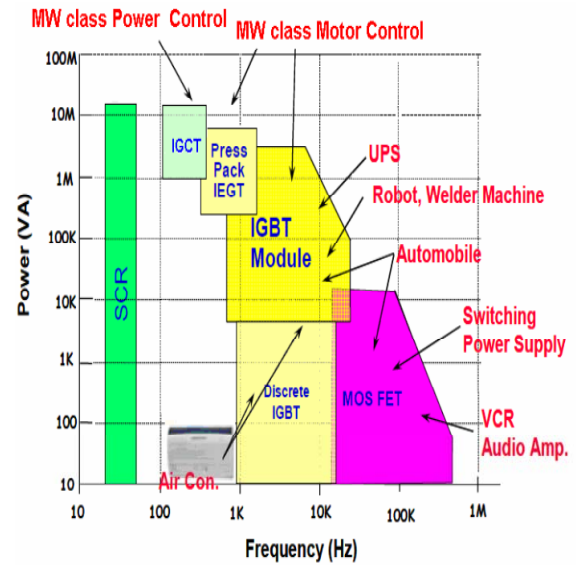


Fig.4 Application fields of power devices

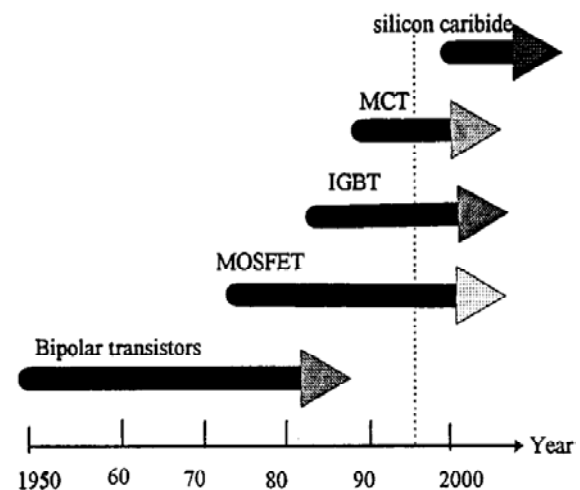


Fig. 5 Current and future power semiconductor devices development direction

## 6. Silicon Carbide Electronic Properties

The electronic parameters of SiC are superior to silicon, thereby offering advantages in terms of electronic performance. For high temperature operation, the most important parameter is the intrinsic carrier concentration i.e. the background density of holes and electrons in the material caused by thermal generation. The generation rate of hole-electron pairs decreases exponentially with the bandgap energy, and the wide bandgap of SiC makes the background carrier concentration orders-of-magnitude smaller than that of silicon, because the maximum operational temperature of a semiconductor device is limited by the temperature where the background density

of holes and electrons becomes comparable to the minimum doping in the device. The intrinsic carrier concentration of silicon and 4H-SiC as a function of temperature. Assuming that the minimum doping in the device is  $10^{15} \text{ cm}^{-3}$ , the maximum junction temperature of a silicon device would be only about 250 °C. In contrast, the maximum junction temperature of the same device made in 4H-SiC would be above 1000 °C. This does not mean that SiC devices can actually be operated at 1000 °C, because other mechanisms will impose lower limits. However, imply that the semiconductor does not impose any electronic limits to the maximum temperature.

Another important electronic parameter is the critical electric field for avalanche breakdown. The critical field in 4H-SiC is almost ten times higher than in silicon. An important figure of merit figure-of-merit,  $\mu_n \epsilon_s E_c^3$ . Because of the high critical field, the Baliga figure of merit in 4H-SiC is about 400 times higher than in silicon. The specific on-resistance (i.e. the resistance-area product) of unipolar devices such as power MOSFETs is inversely proportional to the Baliga figure-of merit. Since this figure-of-merit is 400x higher in SiC, the specific on-resistance in SiC can be up to 400 times lower than in silicon for the same blocking voltage. Results approaching this figure have recently been achieved in actual SiC power devices. Another important advantage of SiC is its high thermal conductivity, 3.3 W/cm K, approximately twice as high as silicon. This facilitates efficient heat removal from the device during high power operation. The electron saturation drift velocity in SiC is also about twice as high as silicon, but the electron mobility is only about 60% of the silicon value. SiC has the distinction of being the only compound semiconductor whose native oxide is silicon dioxide,  $\text{SiO}_2$ . This makes it possible to fabricate the entire range of MOS devices in the material. However, as an insulator,  $\text{SiO}_2$  is not suitable for high temperature operation (i.e.  $T > 250^\circ\text{C}$ ), since it is subject to charge injection at high temperatures and high electric fields. Consequently, SiC devices for high-temperature operation will need to avoid the use of  $\text{SiO}_2$  insulating films in parts of the device where electric fields are also high.

## 7. Energy System Projections

India's economy is projected to grow around 8 times in the next forty-year period while the energy consumption will grow about 3 times and the electricity consumption 5.5 times as shown in Figure 6, (where 2005 figures are taken as the base 100). The per capita gross domestic product is projected to grow 5 times in forty years from a present value of about Rs. 12,000 [2].

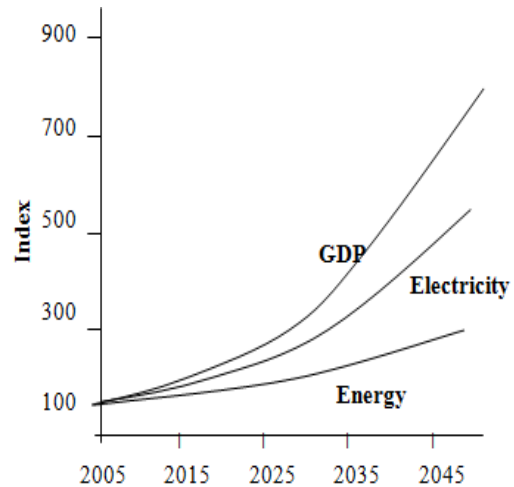


Fig. 6 Growth in economy, energy and electricity

Electricity sector is the fastest growing energy sector. The power produced in India as of April 2007 is 86,425 MW with a deficit of 13.9%. This will increase almost four-folds in the next 40 years as shown in Figure 7, finally reaching a value of 395 GW.

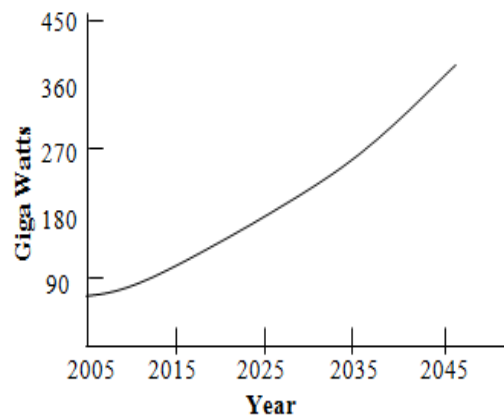


Fig. 7 Projected electric power generation

Inefficiencies and fiscal indiscipline have plagued the transmission and distribution (T&D) system with T&D losses accounting for 35-40% of the total installed capacity. The current focus of T&D system is on integrating nation's power grid. The T&D losses may be reduced to the level of 8% -12 % by adopting High Voltage DC transmission (HVDC) and Flexible AC Transmission Systems (FACTS). HVDC transmissions are widely recognized as being advantageous for long-distance bulk power delivery, asynchronous interconnections, long submarine cable crossing, shared utility right-of-way without degradation of reliability, and to mitigate environmental concerns.



Power electronic converters process gigawatts of power at some point between where it is generated and where it is ultimately utilized; this emphasizes the need for highly efficient power electronic converters and systems in these utility applications. Figure 8 shows a typical cost structure for the converter station [3]. 20% of the converter station cost is due to valves. Presently, thyristors are used in the valves. For high voltage rating of converters of the order of tens and hundreds of KV, many silicon-based power electronic devices are connected in series. With the high voltage capability of wide band-gap semiconductors, replacing the many Si devices by a few wide band-gap semiconductor based power devices is desirable. This will decrease the device count, size, cost of the converter, erection and civil work/maintenance costs, and T&D losses.

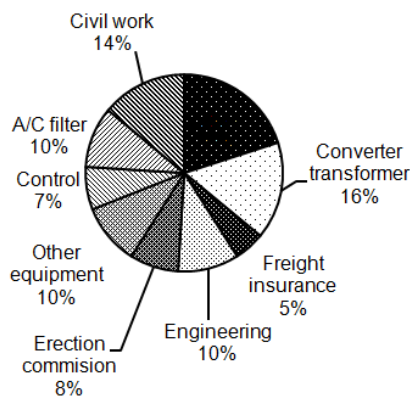


Fig. 8 Cost structure for the converter station

## 8. Energy for the Transport Sector

Indian railways play a major role in the transport system. This requires government policy thrust to railway infrastructure development, better rail connectivity for trade and urban centers, establishing commuter rail services in more cities, increasing operational efficiencies. Increased share of rail in passenger and freight movement is as follows:

- Railway freight share is projected to increase from 37% in 2001 to 50% in 2045 as against 17% in the business-as-usual (BAU) scenario.
- Railway passenger share is projected to increase from 23% in 2001 to 35% in 2045 as against 23% in the BAU scenario.
- Share of electric traction is projected to increase for rail passenger and freight to 80% by 2045 instead of 60% in the BAU scenario [1].

Presently, silicon-based power electronic devices such as diodes, transistors, thyristors, IGBTs, or MOSFETs are used for control in the transportation sector. Their performance is approaching the theoretical limits of fundamental material properties of Si. The emergence of

new power electronic devices based on wide bandgap semiconductor materials such as gallium nitride (GaN) and silicon carbide (SiC) will likely result in substantial improvements in the performance of power electronics converter systems in terms of higher blocking voltages, efficiency, and reliability as well as reduced thermal requirements [4]. The high-VA SiC power electronic devices such as diodes, transistors, thyristors, IGBTs, MOSFETs will significantly impact automobile/locomotion control technologies along with the HVDC transmission/ distribution and micro-grid connections in distributed generation system. The power capacities versus frequency for several types of power devices are shown in Figure 9.

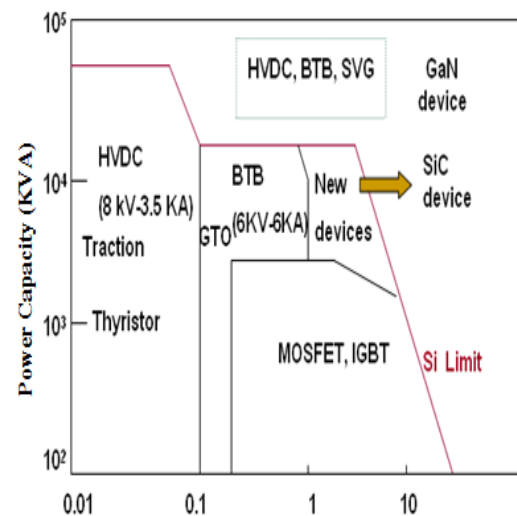


Fig. 9 Power capacities versus frequency for several types of power devices (BTB: back-to-back converter; SVG: Static variable generator)

It shows the correlation between power capacity and frequency of various power devices together with the so-called “Si limit”. The wide bandgap semiconductor devices such as SiC and GaN can be expected to exceed the Si limit, so that expectations are growing that they would realize high-performance converters [5].

## 9. Results and Discussion

In this work, Silicon Carbide discussed some of the results in that pin diode charges shows different voltage levels in Figure 10 to Figure 14. The substrate is selected as Silicon carbide material. The boron and phosphorus is used impurities to form pin diode. Aluminum contact is used as electrode. Thickness of the device is made 20  $\mu\text{m}$  and height is taken as 10  $\mu\text{m}$ . This is shown in Figure 10.

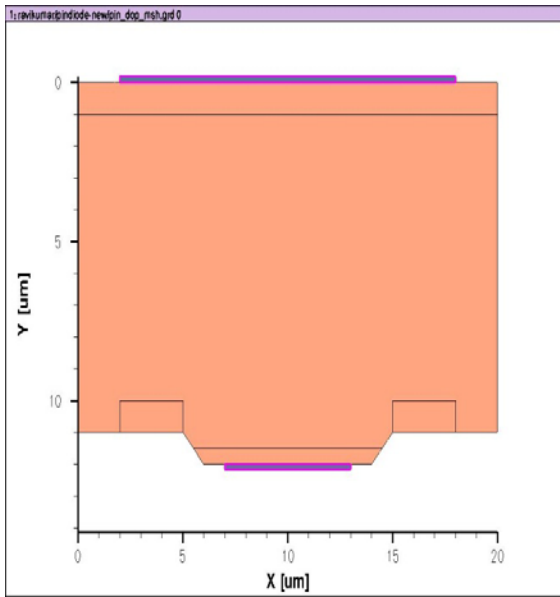


Fig. 10 Structure of Silicon Carbide pin diode

Figure 11 shows the characteristics of pin diode total current in amperes verses anode outer voltage in volts. It is obtained for pin diode total current v/s anode outer voltage. Here, the pin diode forward voltage drop is around 2.6 volts. The current shoots up and increase to 0.008 amperes for anode outer voltage of 7 volts.

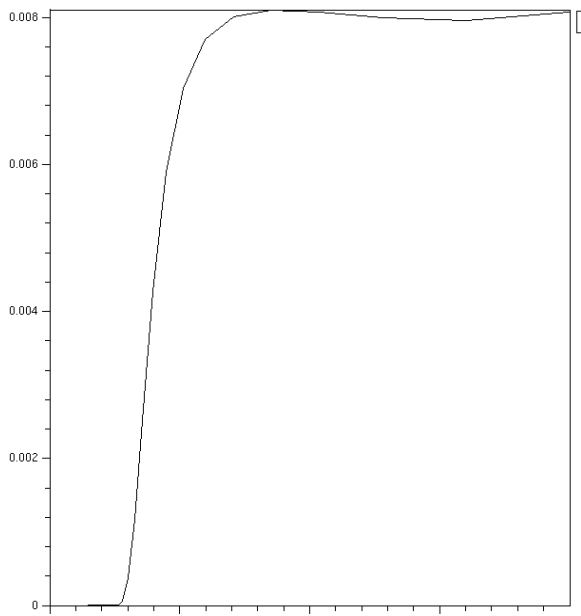


Fig. 11 pin diode total current in amperes verses anode outer voltage in volts.

The pin diode charge verses anode outer voltage is obtained by varying the anode outer voltage and recording the charge. The anode voltage is minimum the charge and

charge increases with increase in the anode outer voltage is shown in Figure 3.

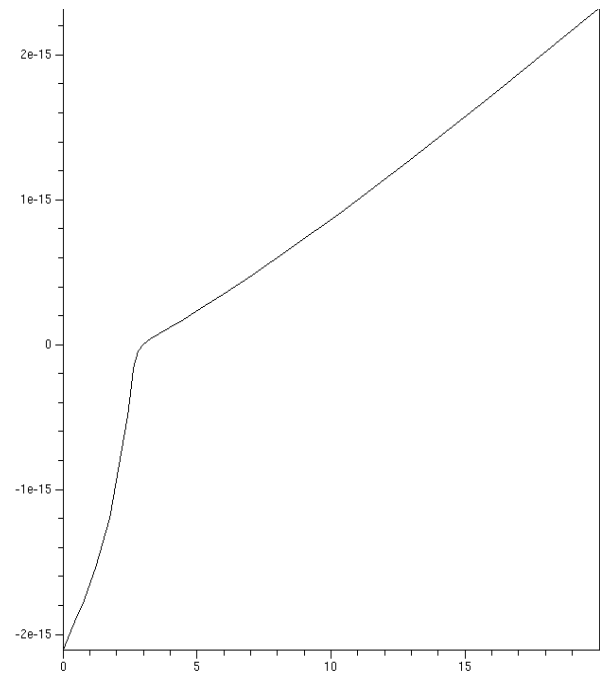


Fig. 12 Pin diode charge verses anode outer voltage

The pin diode obtained by varying the anode inner voltage and recording the eCurrent. Here, as the anode voltage is minimum the charge and charge increases within the anode inner voltage, is shown in Figure 13.

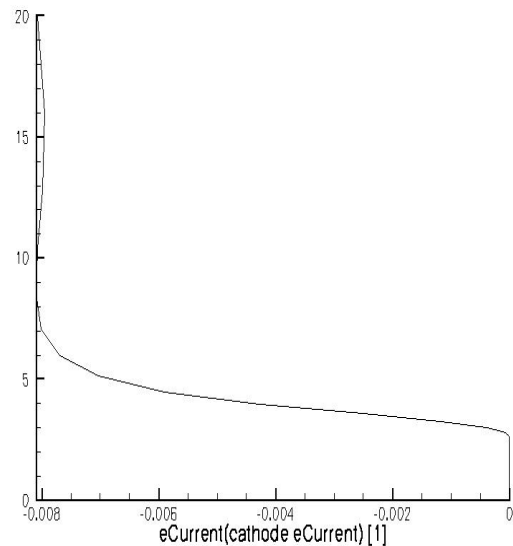


Fig. 13 shows the characteristics of pin diode charge verses anode inner voltage

It shows the eCurrent increases with increase in temperature. The maximum temperature can go up to 1000°C. This is shown in Figure 14.

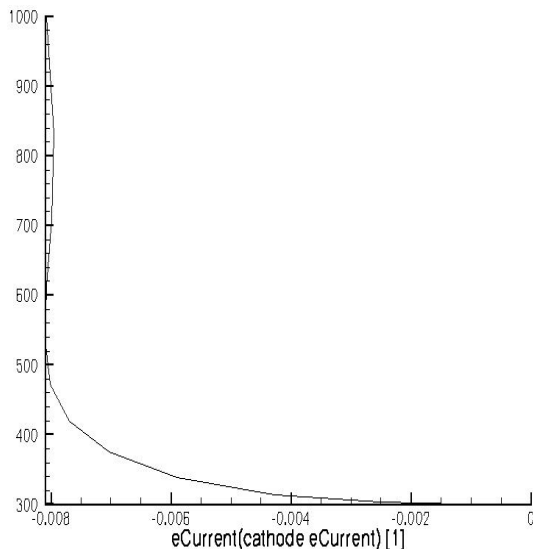


Fig. 14 shows the characteristics of pin diode maximum temperature verses cathode current

## CONCLUSION

In this work, it devoted to realization of an industrial process for the fabrication of SiC diodes for high power and high temperature. To date, there has been no concerted effort to optimize SiC integrated circuits for high-temperature operation, primarily because a strong commercial driver (system pull) has not been present. However, the basic high-temperature capability of the technology is undeniable, and the material quality and fabrication technology have been maturing rapidly. With proper optimization, discrete devices and integrated circuits in SiC should be able to operate reliably at junction temperatures in the 300 -600 °C range. Because of their wide bandgap energy and extreme physical stability, certain classes of SiC devices are also expected to be highly radiation tolerant.

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**Y. S. Ravikumar** received B.E. degree from Bangalore University in 1981 and M.S. degree from BITS, Pilani in 1985. Since 1983 he has been with Electronics and Communication Engineering Department, SIT, Tumkur. At present he is an Asst. Professor in the Department of Telecommunication Engineering, SIT, Tumkur. His research interests are in SiC

device and electronics technology, and power electronics devices.



**K. S. Gurumurthy** received B.E. degree from Mysore University in 1973, M.E. degree from IIT, Roorkee in 1982 and Ph.D. in 1990 from IISc., Bangalore. Title of the thesis is “Behaviour of Electrically Stressed Thin SiO<sub>2</sub> Films for VLSI”. He worked in a small scale Industry from 1973 to 1975 and as lecturer from 1975 to 1980 in the

Dept. of Electronics at B.M.S. College of Engineering, Bangalore. Since 1990, He has been working as an Assistant Professor in the Department of Electronics and CSE, UVCE, B'lore-1. At present he is a Professor. He has over 75 publications to his credit.